

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

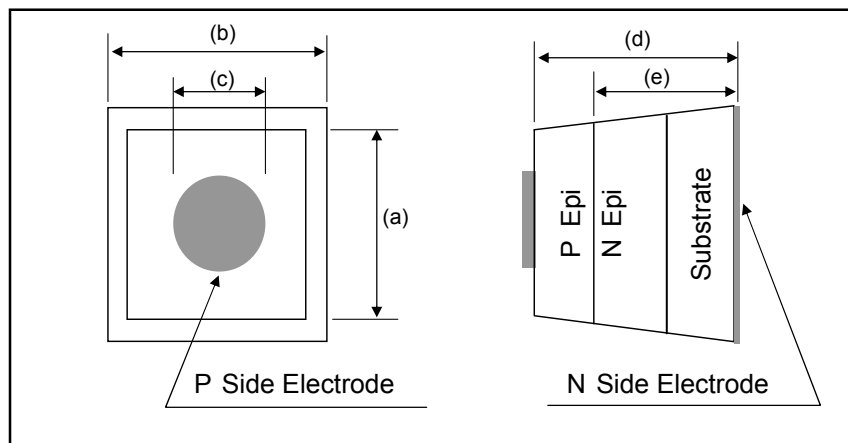
Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.3	1.4	V	IF=20mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	F	1.54		mW	IF=20mA
		G	1.62			
		H(G1)	1.69			
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

※ "Min" of Po is actually "Avg Min"

4. Mechanical Data

(a) Emission Area	-----	8mil x 8mil
(b) Bottom Area	-----	9mil x 9mil
(c) Bonding Pad	-----	110um
(d) Chip Thickness	-----	10mil
(e) Junction Height	-----	6.5mil



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea

Tel. +82 63 839 1111 Fax. +82 63 835 8259

www.auk.co.kr

